OptiMOS™3 Power-MOSFET

Product Summary

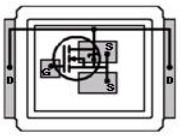
V_{DS}	40	V
$R_{DS(on),max}$	1.5	mΩ
I_D	180	A

Features

- Optimized for high switching frequency DC/DC converter
- Very low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Low parasitic inductance
- Low profile (<0.7 mm)
- 100% avalanche tested
- 100% Rg Tested
- Double-sided cooling
- Pb-free plating; RoHS compliant
- Compatible with DirectFET® package MX footprint and outline [1]
- Qualified according to JEDEC[2] for target applications

MG-WDSON-2

Type	Package	Outline	Marking
BSB015N04NX3 G	MG-WDSON-2	MX	0204



Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	V_{GS}=10 V, T_C=25 °C	180	A
		V_{GS}=10 V, T_C=100 °C	124	
		V_{GS}=10 V, T_A=25 °C, R_{thJA}=45 K/W[2]	35	
Pulsed drain current[3]	$I_{D,pulse}$	T_C=25 °C	400	
Avalanche current, single pulse[4]	I_{AS}	T_C=25 °C	40	
Avalanche energy, single pulse	E_{AS}	I_D=40 A, R_{GS}=25 Ω	290	mJ
Gate source voltage	V_{GS}		±20	V

[1] CanPAK™ uses DirectFET ® technology licensed from International Rectifier Corporation. DirectFET® is a registered trademark of International Rectifier Corporation.

[2] J-STD20 and JESD22

[3] See figure 3 for more detailed information

[4] See figure 13 for more detailed information

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	T_C=25 °C	89	W
		T_A=25 °C, R_{thJA}=45 K/W	2.8	
Operating and storage temperature	T_j, T_{stg}		-40 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}	bottom	-	1.0		K/W
		top	-	-	1.4	
Device on PCB	R_{thJA}	6 cm^2 cooling area[5)]	-	-	45	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250 µA	2	-	4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=40 V, V_{GS}=0 V, T_j=25 °C	-	0.1	10	µA
		V_{DS}=40 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=30 A	-	1.3	1.5	
Gate resistance	R_G		0.2	0.5	1.0	Ω
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=30 A	55	110	-	S

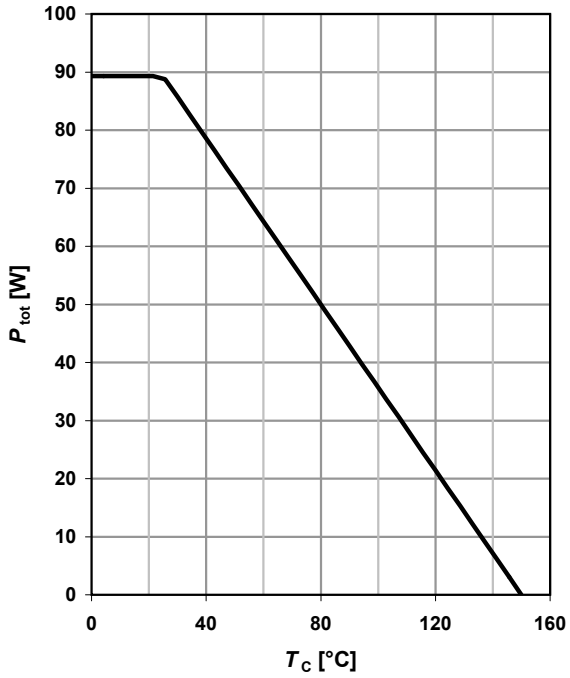
[5)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=20 V, f=1 MHz	-	9000	12000	pF
Output capacitance	C_{oss}		-	2300	3100	
Reverse transfer capacitance	C_{rss}		-	91	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=20 V, V_{GS}=10 V, I_D=30 A, R_G=1.6 Ω	-	23	-	ns
Rise time	t_r		-	6.4	-	
Turn-off delay time	$t_{d(off)}$		-	36	-	
Fall time	t_f		-	7.6	-	
Gate Charge Characteristics[6]						
Gate to source charge	Q_{gs}	V_{DD}=20 V, I_D=30 A, V_{GS}=0 to 10 V	-	41	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	26	-	
Gate to drain charge	Q_{gd}		-	13	-	
Switching charge	Q_{sw}		-	28	-	
Gate charge total	Q_g		-	107	142	
Gate plateau voltage	$V_{plateau}$		-	4.8	-	V
Gate charge total, sync. FET	$Q_{g(sync)}$	V_{DS}=0.1 V, V_{GS}=0 to 10 V	-	101	134	nC
Output charge	Q_{oss}	V_{DD}=20 V, V_{GS}=0 V	-	86	-	
Reverse Diode						
Diode continuous forward current	I_S	T_C=25 °C	-	-	89	A
Diode pulse current	$I_{S,pulse}$		-	-	400	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=30 A, T_j=25 °C	-	0.81	-	V
Reverse recovery charge	Q_{rr}	V_R=15 V, I_F=I_S, di_F/dt=400 A/µs	-	-	50	nC

[6] See figure 16 for gate charge parameter definition

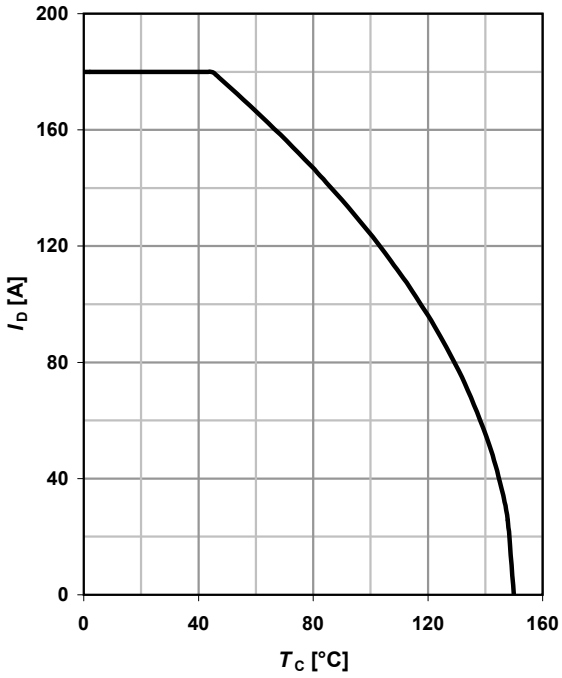
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

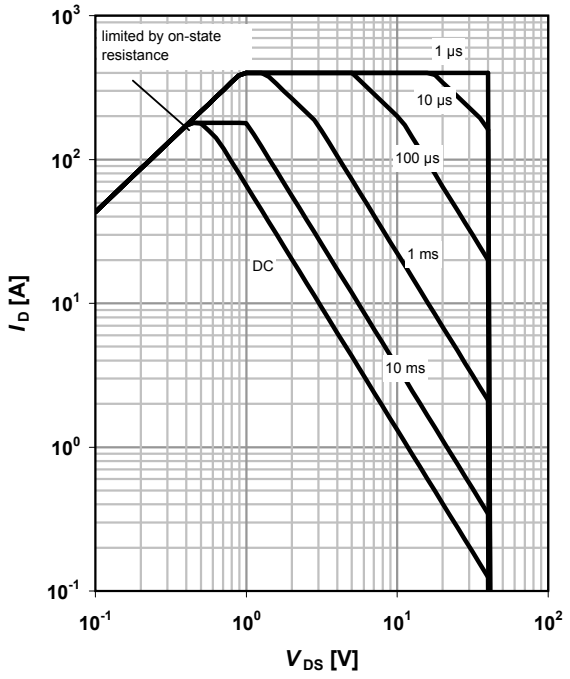
$I_D=f(T_C)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

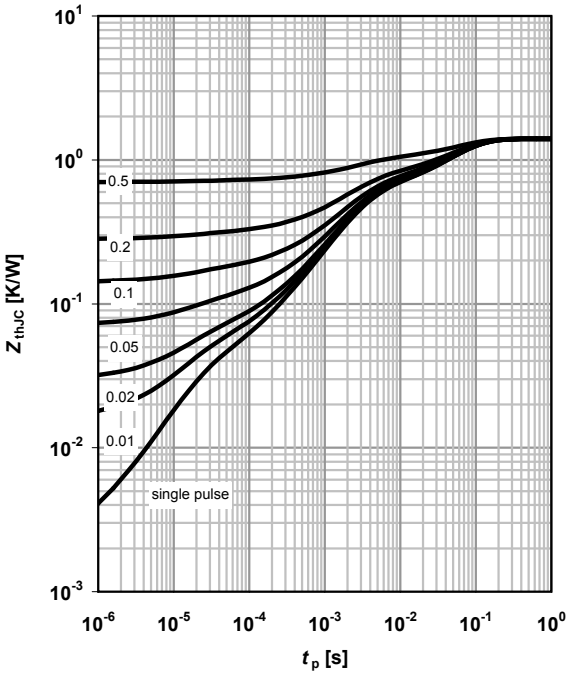
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

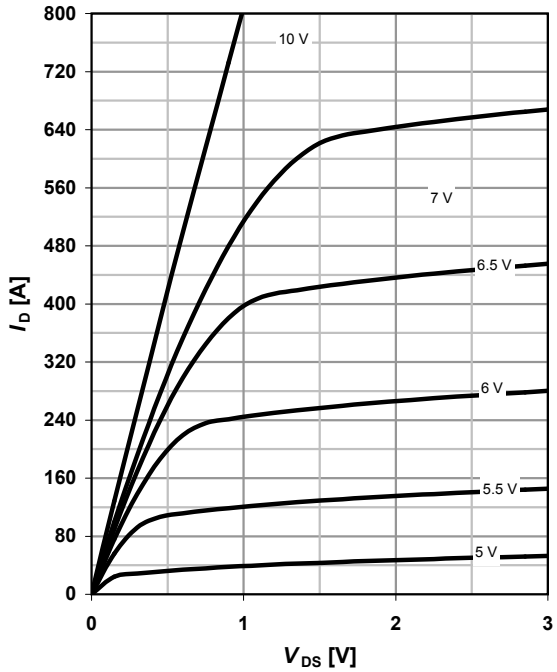
parameter: $D=t_p/T$



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

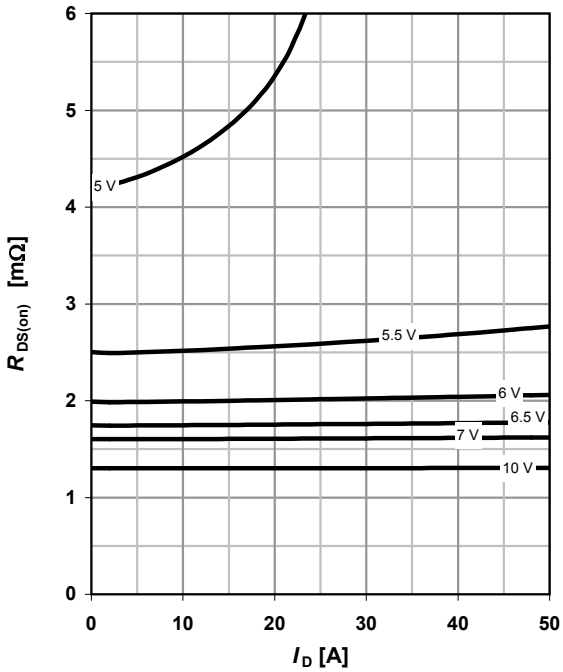
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}$=f(I_D); T_j=25 °C

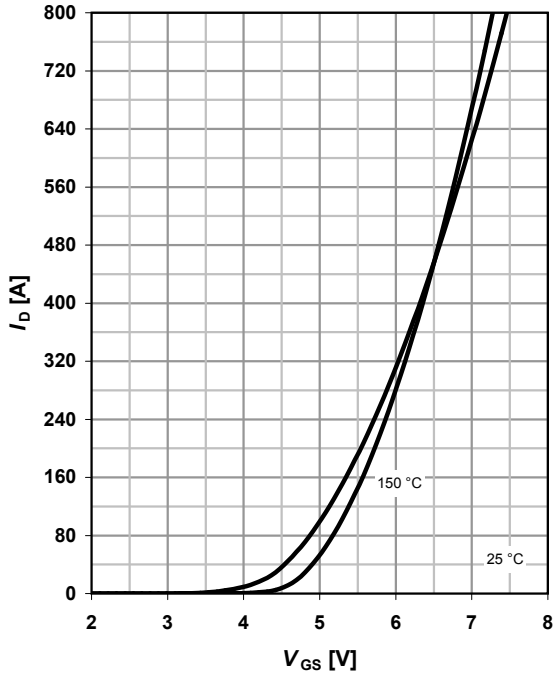
parameter: V_{GS}



7 Typ. transfer characteristics

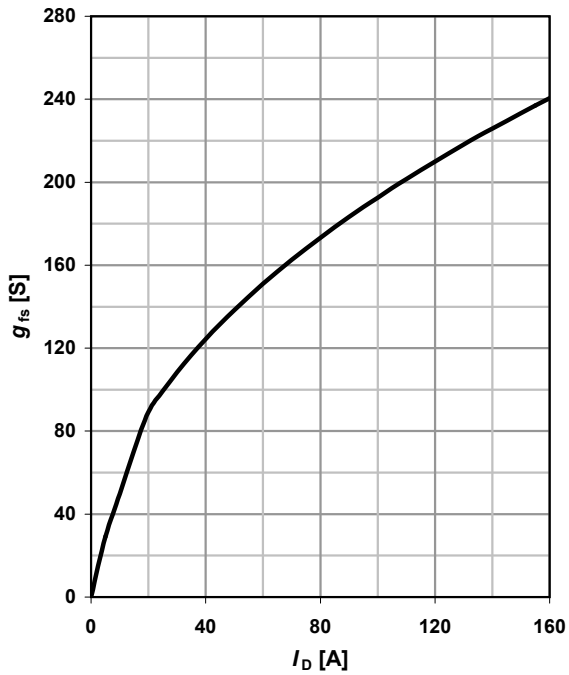
I_D=f(V_{GS}); $|V_{DS}|>2|I_D|R_{DS(on)max}$

parameter: T_j



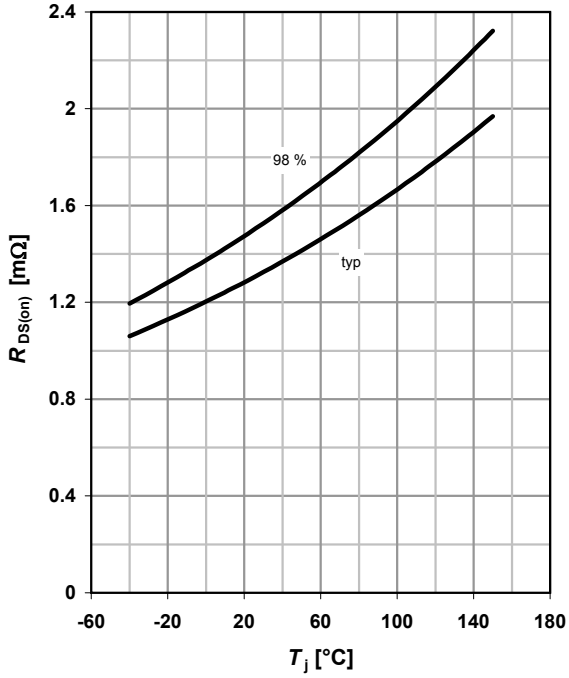
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C



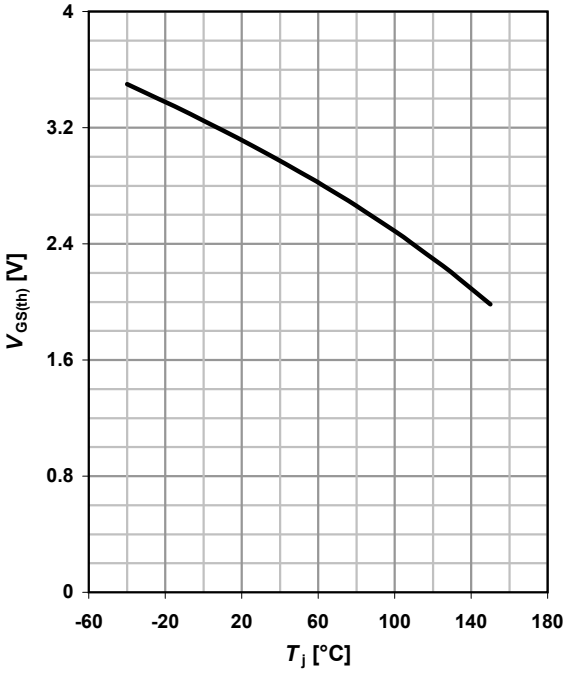
9 Drain-source on-state resistance

$R_{DS(on)}$=f(T_j); I_D=30 A; V_{GS}=10 V



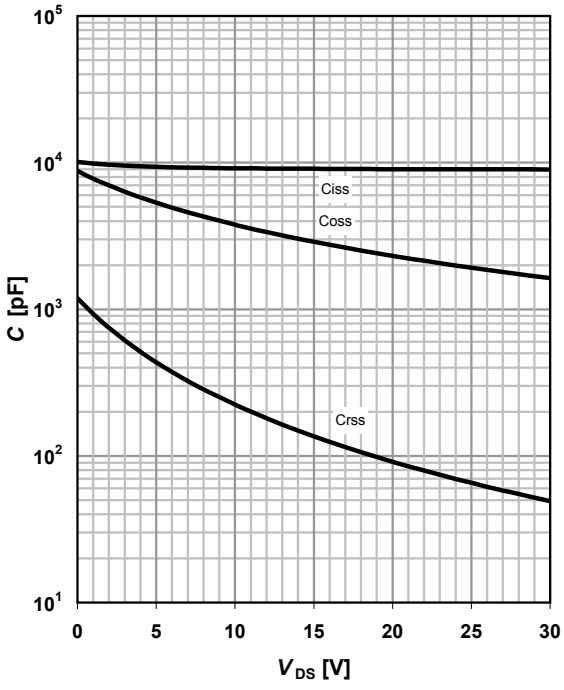
10 Typ. gate threshold voltage

$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; I_D=250 µA



11 Typ. capacitances

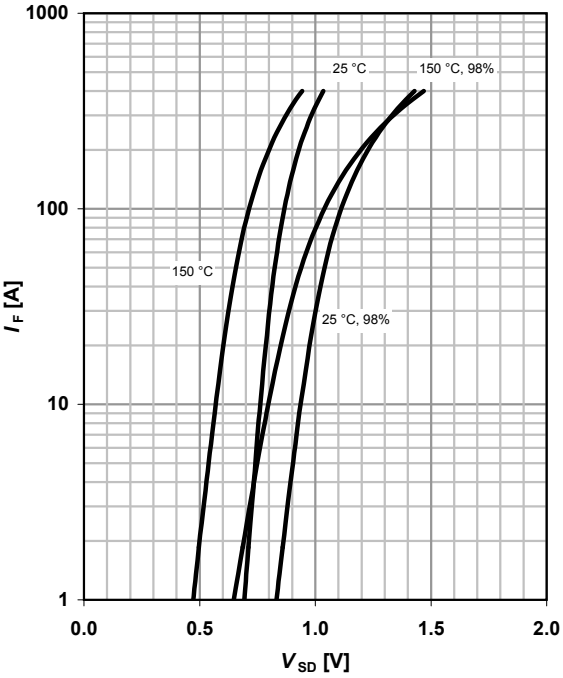
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

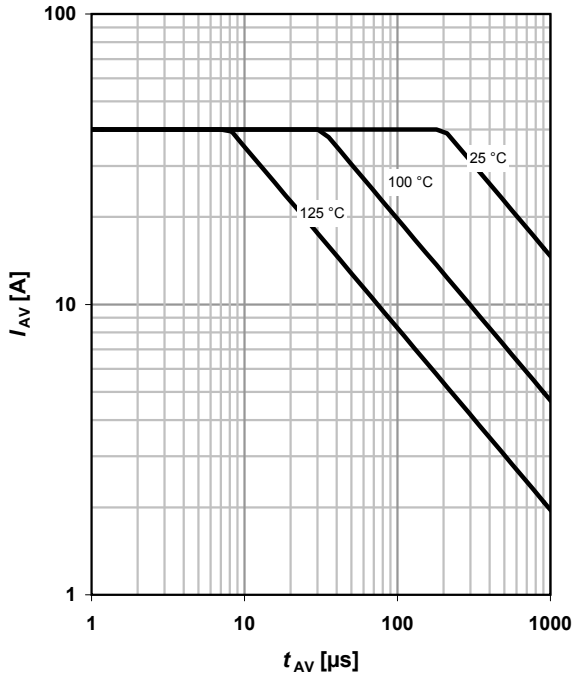
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

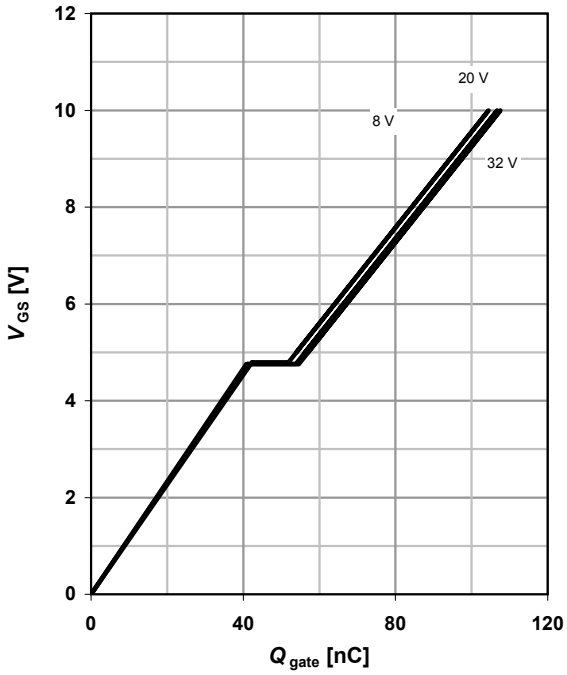
parameter: $T_{j(start)}$



14 Typ. gate charge

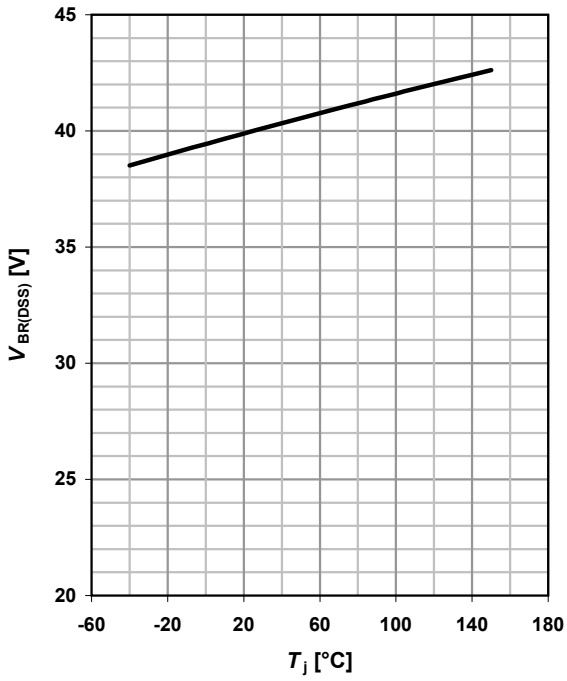
V_{GS}=f(Q_{gate}); I_D=30 A pulsed

parameter: V_{DD}

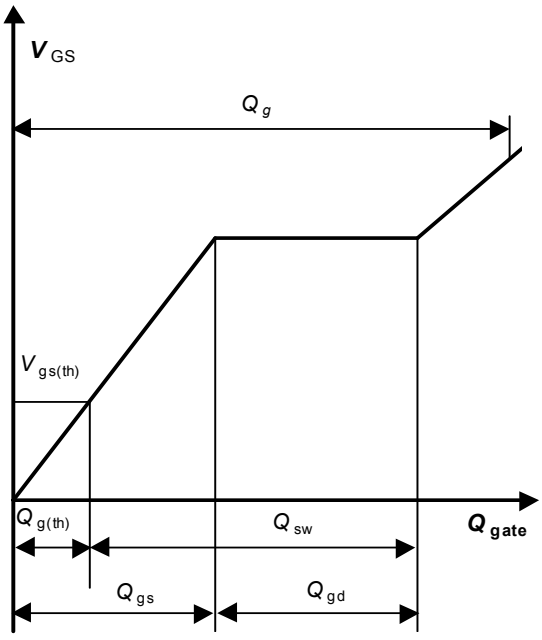


15 Drain-source breakdown voltage

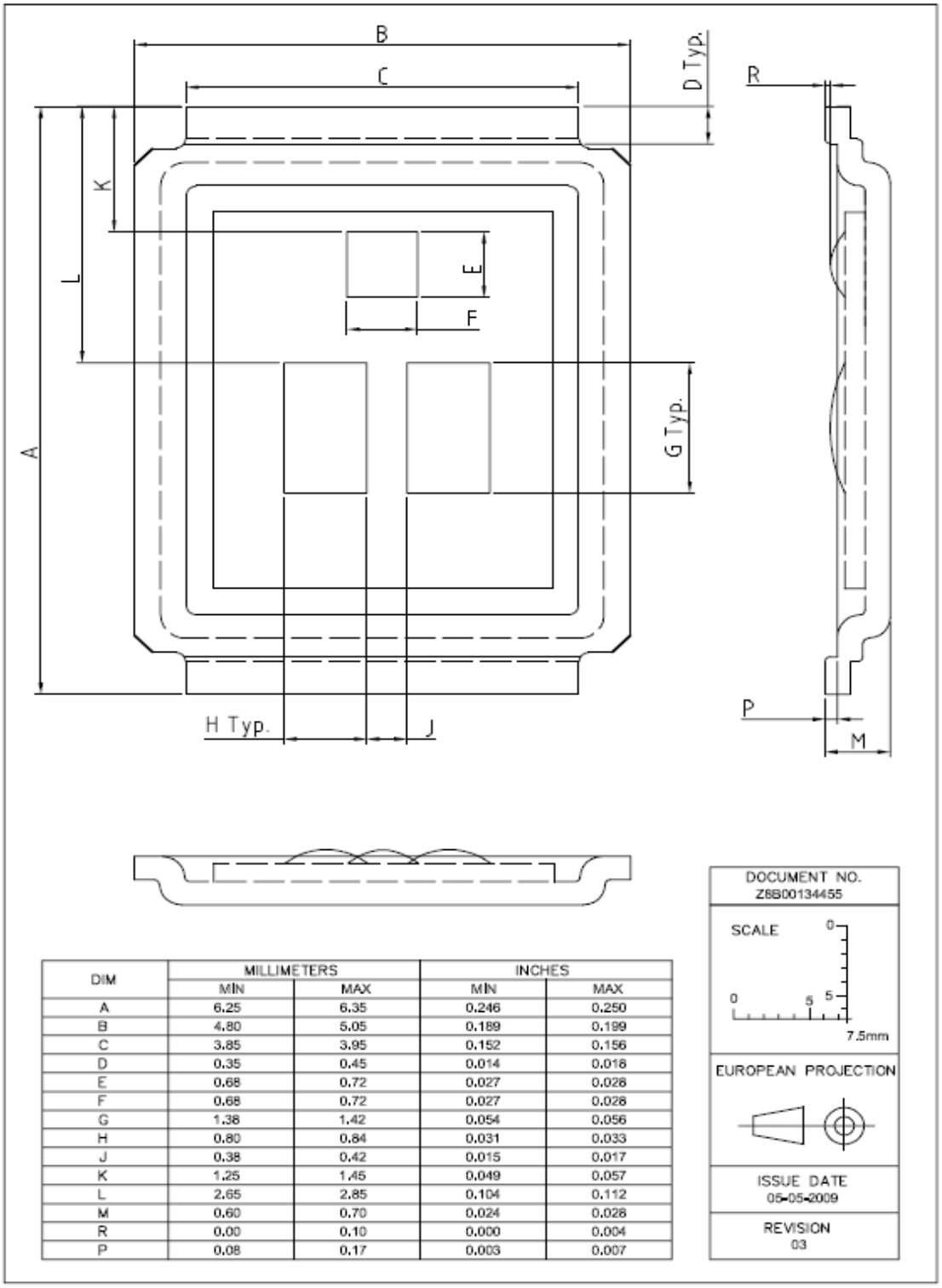
$V_{BR(DSS)}$=f(T_j); I_D=1 mA



16 Gate charge waveforms



MG–WDSON–2



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.25	6.35	0.246	0.250
B	4.80	5.05	0.189	0.199
C	3.85	3.95	0.152	0.156
D	0.35	0.45	0.014	0.018
E	0.68	0.72	0.027	0.028
F	0.68	0.72	0.027	0.028
G	1.38	1.42	0.054	0.056
H	0.80	0.84	0.031	0.033
J	0.38	0.42	0.015	0.017
K	1.25	1.45	0.049	0.057
L	2.65	2.85	0.104	0.112
M	0.60	0.70	0.024	0.028
R	0.00	0.10	0.000	0.004
P	0.08	0.17	0.003	0.007

DOCUMENT NO.
Z8B00134455

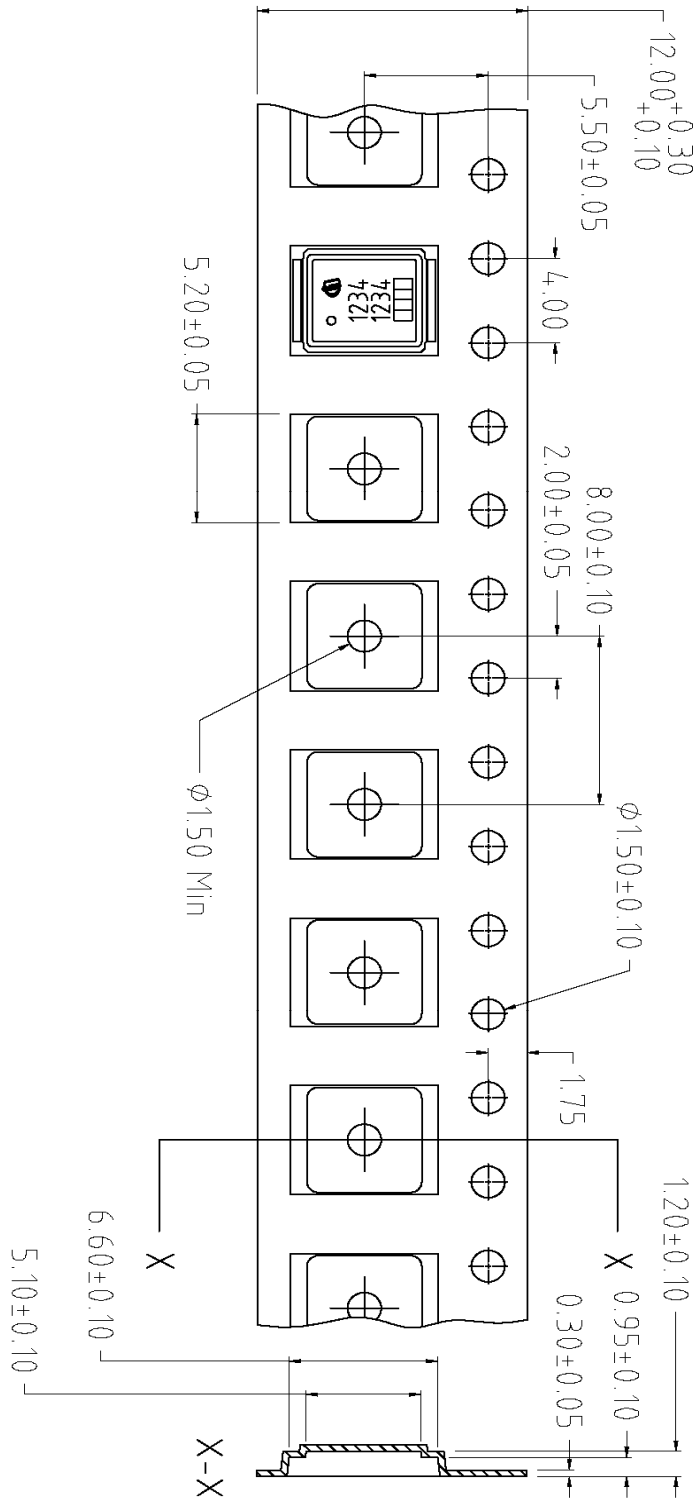
SCALE 0 5 5 7.5mm

EUROPEAN PROJECTION

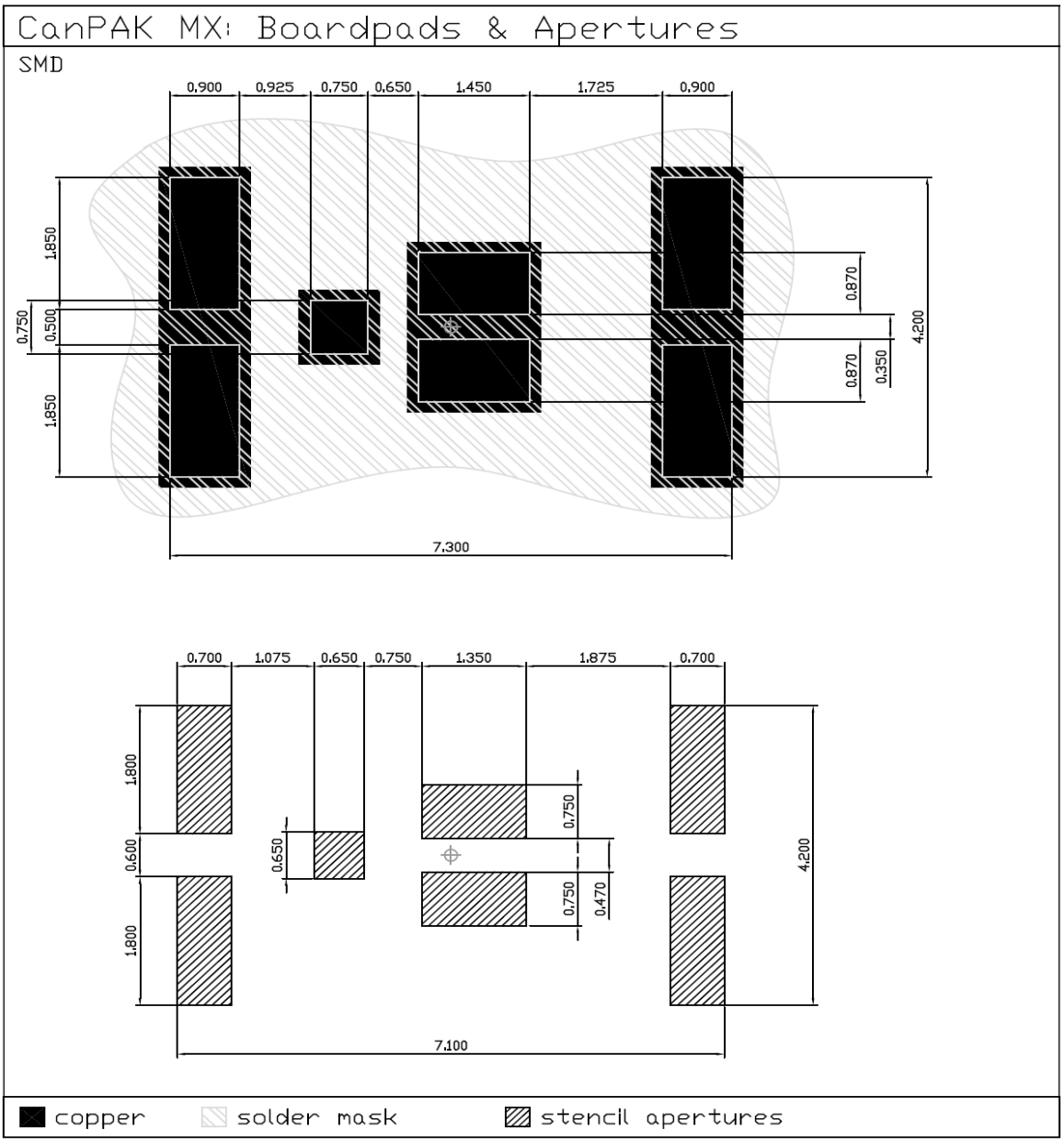
ISSUE DATE
05-05-2009

REVISION
03

Package Outline **MG-WDSON-2**



Dimensions in mm



Dimensions in mm

Recommended stencil thickness 150 µm

Published by

Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer
The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information
For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings
Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.
Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.